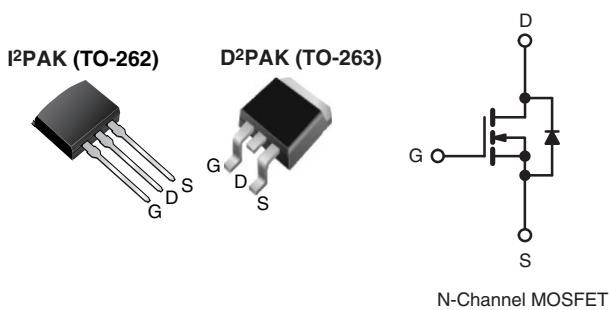


## Power MOSFET

PRODUCT SUMMARY		
$V_{DS}$ (V)	600	
$R_{DS(on)}$ ( $\Omega$ )	$V_{GS} = 10$ V	2.2
$Q_g$ (Max.) (nC)	31	
$Q_{gs}$ (nC)	4.6	
$Q_{gd}$ (nC)	17	
Configuration	Single	



### FEATURES

- Halogen-free According to IEC 61249-2-21
- Definition
- Surface Mount (IRFBC30S, SiHFBC30S)
- Low-Profile Through-Hole (IRFBC30L, SiHFBC30L)
- Available in Tape and Reel (IRFBC30S, SiHFBC30S)
- Dynamic dV/dt Rating
- 150 °C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Compliant to RoHS Directive 2002/95/EC



### DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The D<sup>2</sup>PAK is a surface mount power package capable of the accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The D<sup>2</sup>PAK is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0 W in a typical surface mount application. The through-hole version (IRFBC30L, SiHFBC30L) is a available for low-profile applications.

ORDERING INFORMATION			
Package	D <sup>2</sup> PAK (TO-263)	D <sup>2</sup> PAK (TO-263)	I <sup>2</sup> PAK (TO-262)
Lead (Pb)-free and Halogen-free	SiHFBC30S-GE3	SiHFBC30STR-GE3 <sup>a</sup>	SiHFBC30L-GE3
Lead (Pb)-free	IRFBC30SPbF	IRFBC30STRLPbF <sup>a</sup>	IRFBC30LPbF
	SiHFBC30S-E3	SiHFBC30STL-E3 <sup>a</sup>	SiHFBC30L-E3

#### Note

a. See device orientation.

ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted)			
PARAMETER		SYMBOL	LIMIT
Drain-Source Voltage		$V_{DS}$	600
Gate-Source Voltage		$V_{GS}$	$\pm 20$
Continuous Drain Current <sup>e</sup>	$V_{GS}$ at 10 V	$I_D$	3.6
	$T_C = 25$ °C		2.3
Pulsed Drain Current <sup>a, e</sup>		$I_{DM}$	14
Linear Derating Factor			0.59
Single Pulse Avalanche Energy <sup>b, e</sup>		$E_{AS}$	290
Avalanche Current <sup>a</sup>		$I_{AR}$	3.6
Repetitive Avalanche Energy <sup>a</sup>		$E_{AR}$	7.4
Maximum Power Dissipation	$T_A = 25$ °C	$P_D$	3.1
	$T_C = 25$ °C		74
Peak Diode Recovery dV/dt <sup>c, e</sup>		$dV/dt$	3.0
Operating Junction and Storage Temperature Range	$T_J, T_{Stg}$		- 55 to + 150
Soldering Recommendations (Peak Temperature)	for 10 s		300 <sup>d</sup>

#### Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- b.  $V_{DD} = 50$  V, starting  $T_J = 25$  °C,  $L = 41$  mH,  $R_g = 25$   $\Omega$ ,  $I_{AS} = 3.6$  A (see fig. 12).
- c.  $I_{SD} \leq 3.6$  A,  $dI/dt \leq 60$  A/ $\mu$ s,  $V_{DD} \leq V_{DS}$ ,  $T_J \leq 150$  °C.
- d. 1.6 mm from case.
- e. Uses IRFBC30, SiHFBC30 data and test conditions.

\* Pb containing terminations are not RoHS compliant, exemptions may apply

**THERMAL RESISTANCE RATINGS**

PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient (PCB Mounted, steady-state) <sup>a</sup>	$R_{thJA}$	-	40	°C/W
Maximum Junction-to-Case (Drain)	$R_{thJC}$	-	1.7	

**Note**

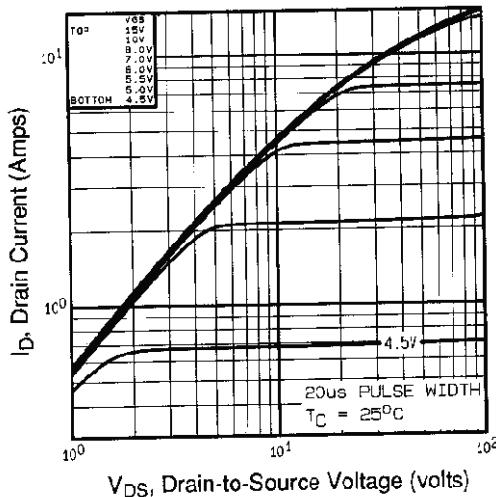
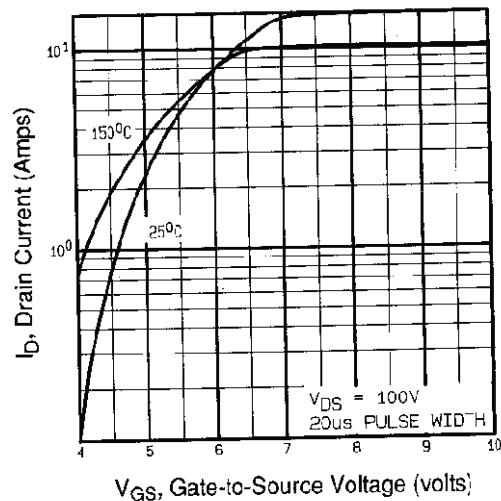
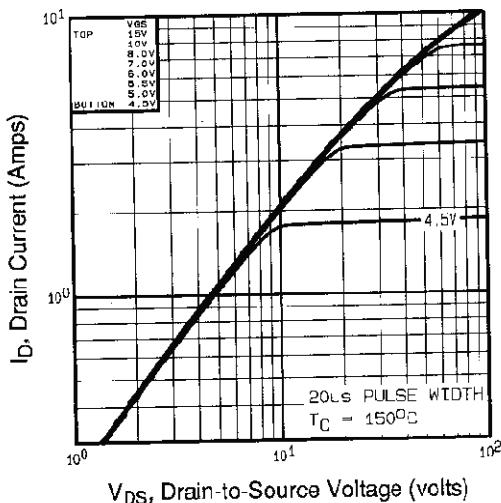
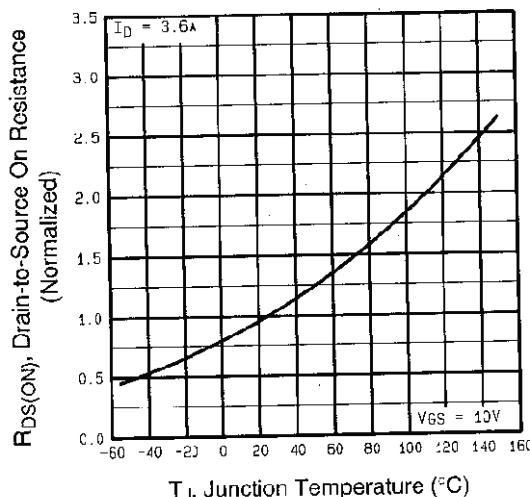
a. When mounted on 1" square PCB (FR-4 or G-10 material).  
 For recommended footprint and soldering techniques refer to application note #AN-994.

**SPECIFICATIONS (T<sub>J</sub> = 25 °C, unless otherwise noted)**

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
<b>Static</b>								
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0$ , $I_D = 250 \mu A$		600	-	-	V	
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to 25 °C, $I_D = 1 \text{ mA}^c$		-	0.62	-	V/°C	
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$		2.0	-	4.0	V	
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 600 \text{ V}$ , $V_{GS} = 0 \text{ V}$		-	-	100	μA	
		$V_{DS} = 480 \text{ V}$ , $V_{GS} = 0 \text{ V}$ , $T_J = 125 \text{ °C}$		-	-	500		
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$	$I_D = 2.2 \text{ A}^b$	-	-	2.2	Ω	
Forward Transconductance	$g_{fs}$	$V_{DS} = 50 \text{ V}$ , $I_D = 2.2 \text{ A}^c$		2.5	-	-	S	
<b>Dynamic</b>								
Input Capacitance	$C_{iss}$	$V_{GS} = 0 \text{ V}$ , $V_{DS} = 25 \text{ V}$ , $f = 1.0 \text{ MHz}$ , see fig. 5 <sup>c</sup>		-	660	-	pF	
Output Capacitance	$C_{oss}$			-	86	-		
Reverse Transfer Capacitance	$C_{rss}$			-	19	-		
Total Gate Charge	$Q_g$	$V_{GS} = 10 \text{ V}$	$I_D = 3.6 \text{ A}$ , $V_{DS} = 360 \text{ V}$ , see fig. 6 and 13 <sup>b, c</sup>	-	-	31	nC	
Gate-Source Charge	$Q_{gs}$			-	-	4.6		
Gate-Drain Charge	$Q_{gd}$			-	-	17		
Turn-On Delay Time	$t_{d(on)}$			-	11	-		
Rise Time	$t_r$	$V_{DD} = 300 \text{ V}$ , $I_D = 3.6 \text{ A}$ , $R_g = 12 \Omega$ , $R_D = 82 \Omega$ , see fig. 10 <sup>b, c</sup>		-	13	-	ns	
Turn-Off Delay Time	$t_{d(off)}$			-	35	-		
Fall Time	$t_f$			-	14	-		
Internal Source Inductance	$L_s$	Between lead, and center of die contact		-	7.5	-	nH	
<b>Drain-Source Body Diode Characteristics</b>								
Continuous Source-Drain Diode Current	$I_s$	MOSFET symbol showing the integral reverse p - n junction diode		-	-	3.6	A	
Pulsed Diode Forward Current <sup>a</sup>	$I_{SM}$			-	-	14		
Body Diode Voltage	$V_{SD}$	$T_J = 25 \text{ °C}$ , $I_s = 3.6 \text{ A}$ , $V_{GS} = 0 \text{ V}^b$		-	-	1.6	V	
Body Diode Reverse Recovery Time	$t_{rr}$	$T_J = 25 \text{ °C}$ , $I_F = 3.6 \text{ A}$ , $dI/dt = 100 \text{ A}/\mu\text{s}^{b, c}$		-	370	810	ns	
Body Diode Reverse Recovery Charge	$Q_{rr}$			-	2.0	4.2	μC	
Forward Turn-On Time	$t_{on}$	Intrinsic turn-on time is negligible (turn-on is dominated by $L_s$ and $L_D$ )						

**Notes**

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).  
 b. Pulse width ≤ 300 μs; duty cycle ≤ 2 %.  
 c. Uses IRFBC30, SiHFBC30 data and test conditions.

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Fig. 1 - Typical Output Characteristics**

**Fig. 3 - Typical Transfer Characteristics**

**Fig. 2 - Typical Output Characteristics**

**Fig. 4 - Normalized On-Resistance vs. Temperature**

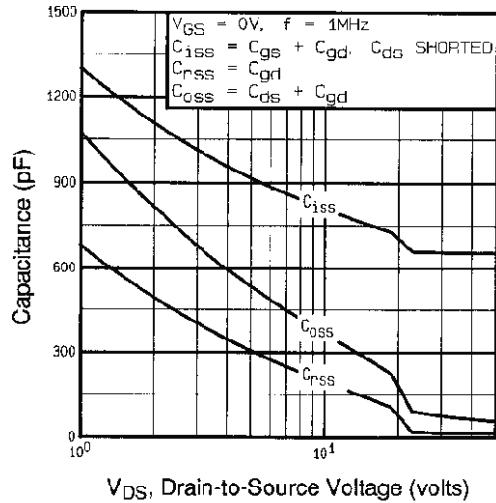


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

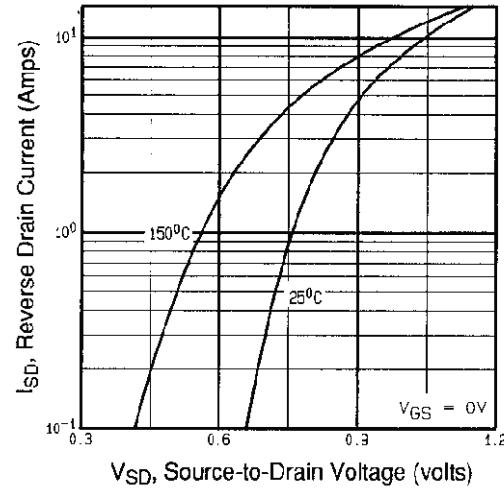


Fig. 7 - Typical Source-Drain Diode Forward Voltage

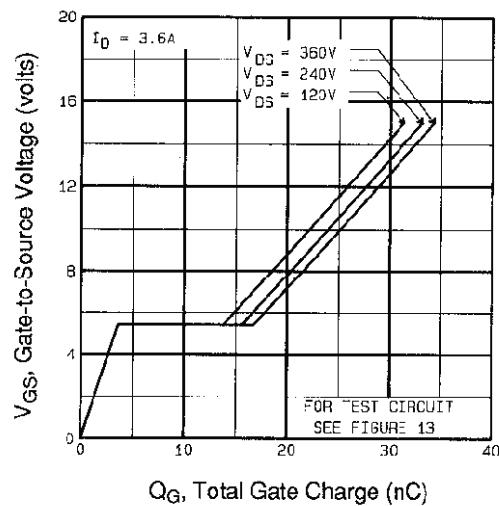


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

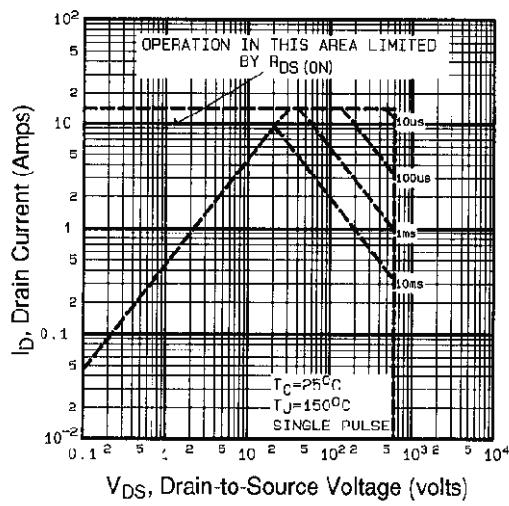


Fig. 8 - Maximum Safe Operating Area

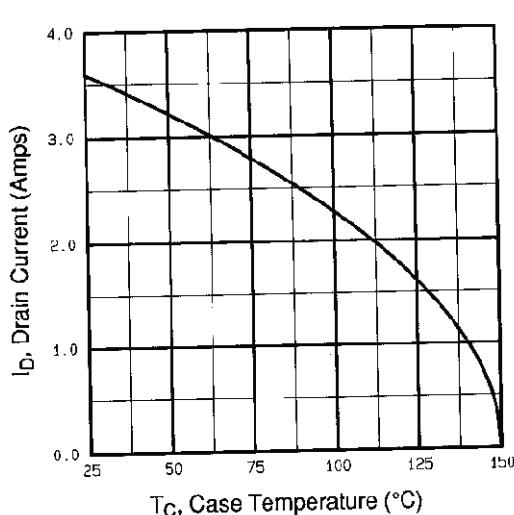


Fig. 9 - Maximum Drain Current vs. Case Temperature

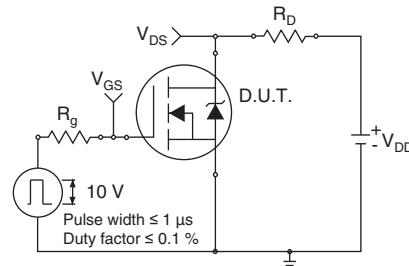


Fig. 10a - Switching Time Test Circuit

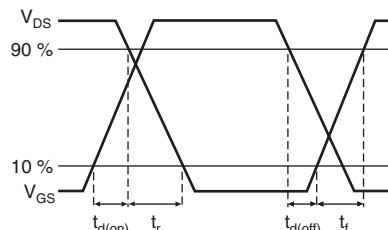


Fig. 10b - Switching Time Waveforms

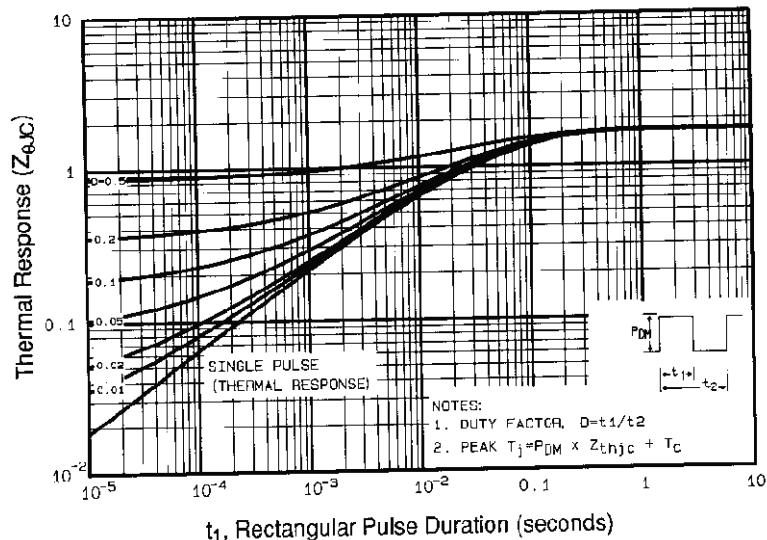


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

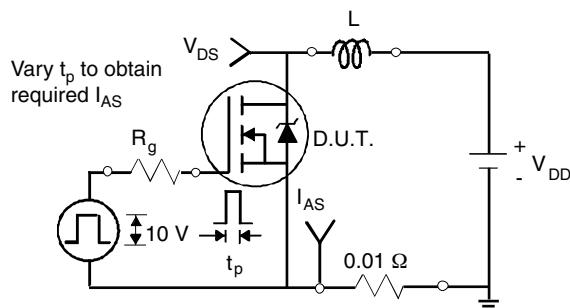


Fig. 12a - Unclamped Inductive Test Circuit

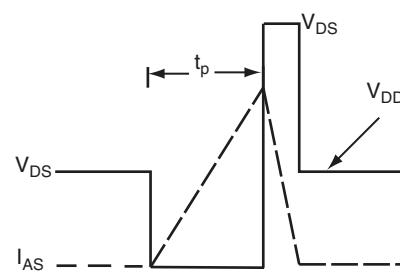


Fig. 12b - Unclamped Inductive Waveforms

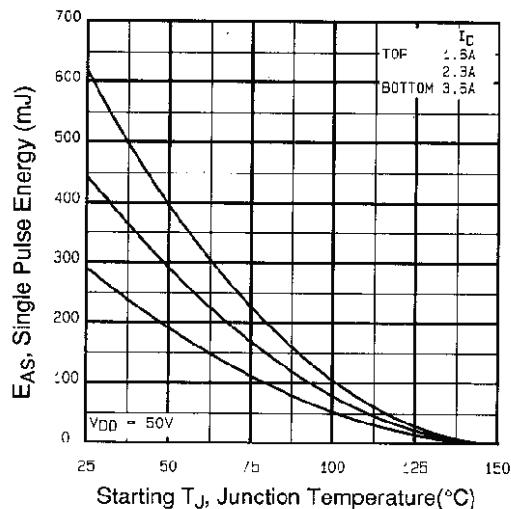


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

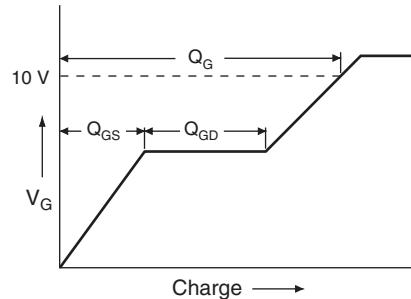


Fig. 13a - Maximum Avalanche Energy vs. Drain Current

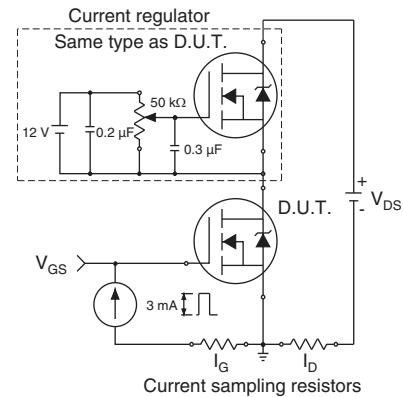
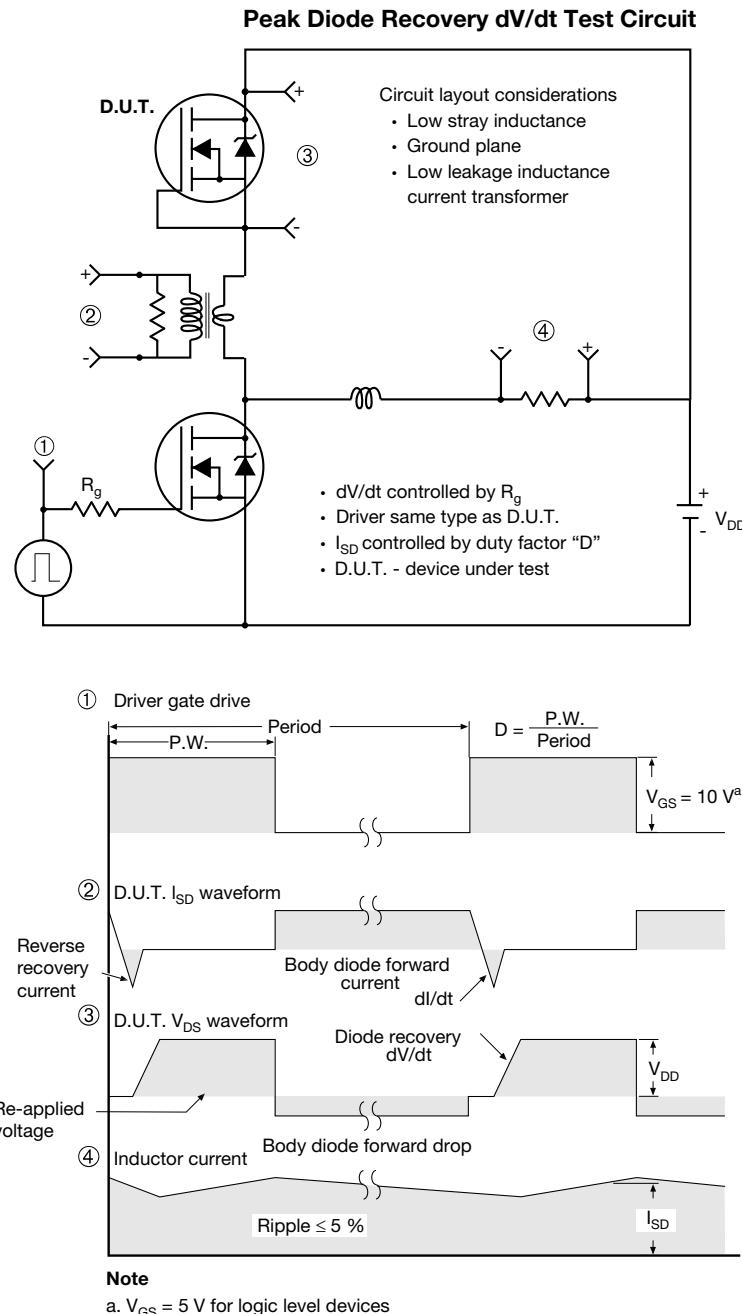
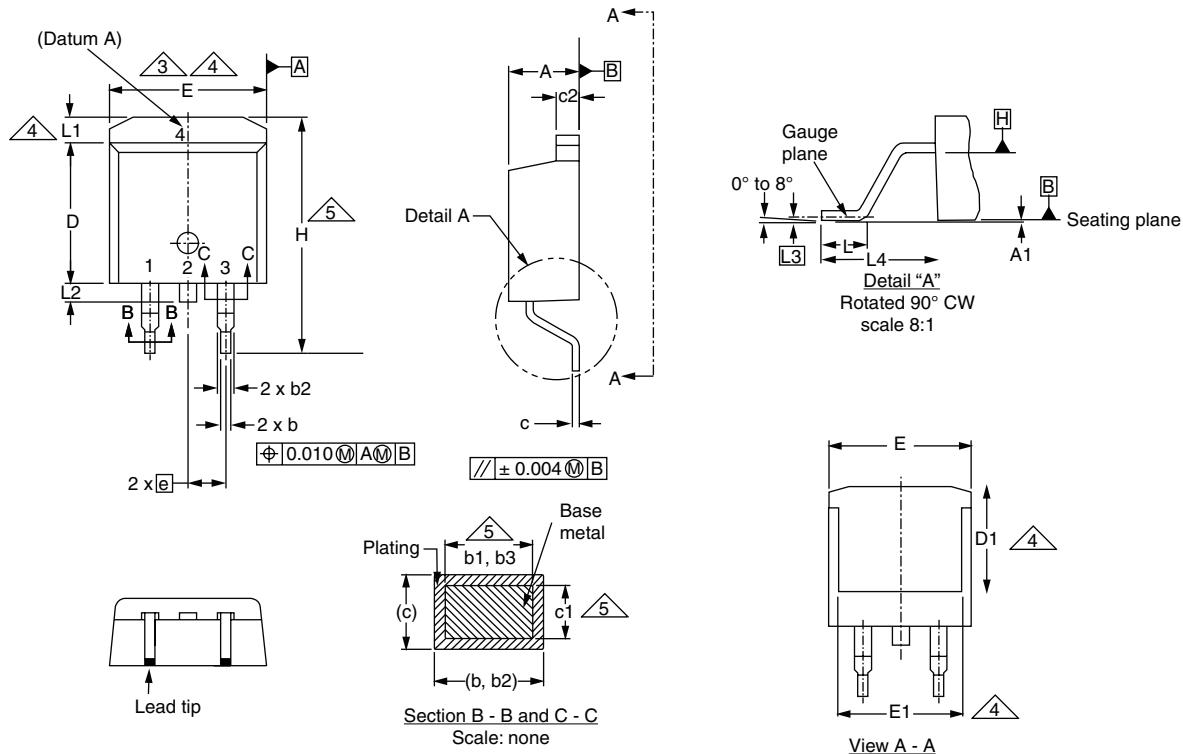


Fig. 13b - Gate Charge Test Circuit


**Fig. 14 - For N-Channel**

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### TO-263AB (HIGH VOLTAGE)



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.06	4.83	0.160	0.190
A1	0.00	0.25	0.000	0.010
b	0.51	0.99	0.020	0.039
b1	0.51	0.89	0.020	0.035
b2	1.14	1.78	0.045	0.070
b3	1.14	1.73	0.045	0.068
c	0.38	0.74	0.015	0.029
c1	0.38	0.58	0.015	0.023
c2	1.14	1.65	0.045	0.065
D	8.38	9.65	0.330	0.380

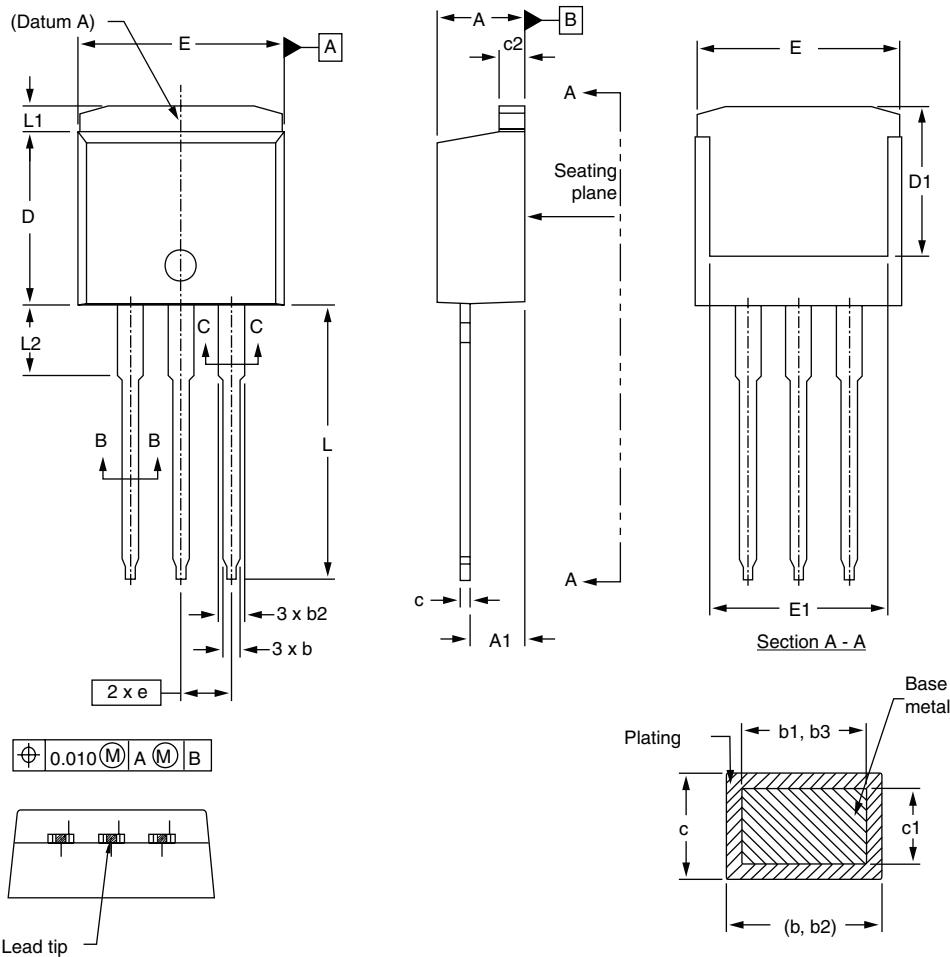
ECN: S-82110-Rev. A, 15-Sep-08  
DWG: 5970

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
D1	6.86	-	0.270	-
E	9.65	10.67	0.380	0.420
E1	6.22	-	0.245	-
e	2.54 BSC		0.100 BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	-	1.65	-	0.066
L2	-	1.78	-	0.070
L3	0.25 BSC		0.010 BSC	
L4	4.78	5.28	0.188	0.208

#### Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimensions are shown in millimeters (inches).
3. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body at datum A.
4. Thermal PAD contour optional within dimension E, L1, D1 and E1.
5. Dimension b1 and c1 apply to base metal only.
6. Datum A and B to be determined at datum plane H.
7. Outline conforms to JEDEC outline to TO-263AB.

### I<sup>2</sup>PAK (TO-262) (HIGH VOLTAGE)



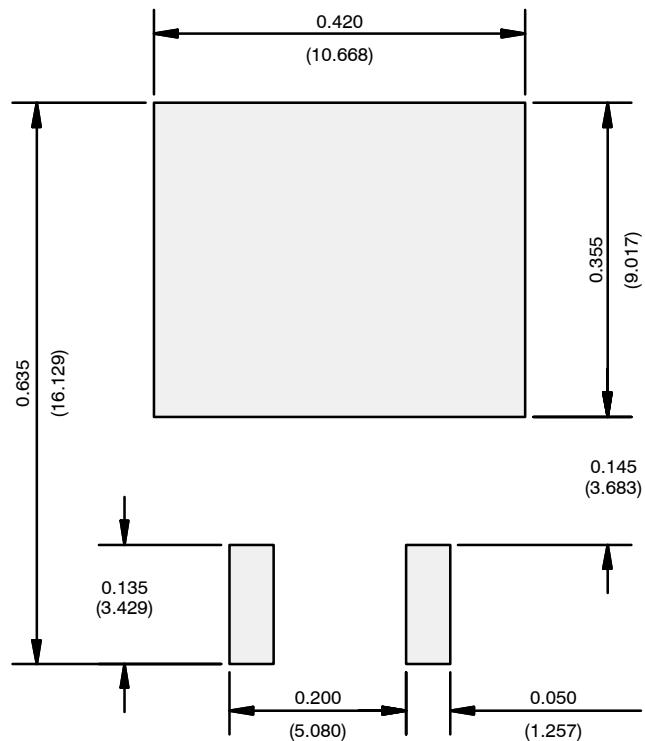
DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.06	4.83	0.160	0.190
A1	2.03	3.02	0.080	0.119
b	0.51	0.99	0.020	0.039
b1	0.51	0.89	0.020	0.035
b2	1.14	1.78	0.045	0.070
b3	1.14	1.73	0.045	0.068
c	0.38	0.74	0.015	0.029
c1	0.38	0.58	0.015	0.023
c2	1.14	1.65	0.045	0.065

ECN: S-82442-Rev. A, 27-Oct-08  
DWG: 5977

#### Notes

- Dimensioning and tolerancing per ASME Y14.5M-1994.
- Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outmost extremes of the plastic body.
- Thermal pad contour optional within dimension E, L1, D1, and E1.
- Dimension b1 and c1 apply to base metal only.

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
D	8.38	9.65	0.330	0.380
D1	6.86	-	0.270	-
E	9.65	10.67	0.380	0.420
E1	6.22	-	0.245	-
e	2.54 BSC		0.100 BSC	
L	13.46	14.10	0.530	0.555
L1	-	1.65	-	0.065
L2	3.56	3.71	0.140	0.146

**RECOMMENDED MINIMUM PADS FOR D<sup>2</sup>PAK: 3-Lead**

Recommended Minimum Pads  
Dimensions in Inches/(mm)

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